## **Bipolar Transistor** Low Power





#### Features:

- PNP Silicon Planar switching Transistors
- General Purpose Transistor
- **Pin Configuration** 1. Emitter

Base
Collector



#### **Absolute Maximum Ratings**

Description	Symbol	Value	Units	
Collector Emitter Voltage	Vceo	40		
Collector Base Voltage	Vсво	60	V	
Emitter Base Voltage	Vebo	5		
Collector Current Continuous	lc	600	mA	
Power Dissipation at T <sub>A</sub> = 25°C Derate above 25°C		600 3.43	W	
Power Dissipation at Tc = 25°C Derate above 25°C	PD	3 17	mW/°C	
Operating and Storage Junction Temperature Range	Tj, Tstg	-65 to +200	°C	

#### Electrical Characteristics: (Tc = +25°C unless specified otherwise)

Description	Symbol	Test Condition	Min.	Max.	Units
Collector Emitter Voltage	*Vceo	Ic = 10mA, I <sub>B</sub> = 0	40	-	
Collector Base Voltage	Vсво Ic = 10µА, IE = 0		60	-	V
Emmiter Base Voltage	Vebo	$I_E = 10 \mu A$ , $I_C = 0$	5	-	
Collector Cut off Current	ICEX	Vce = 30V, VBE = 0.5V	-	50	nA
		Vcb = 50V, IE = 0	-		nA
Collector Cut off Current	Ісво	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0, Та = 150°С	-	20	μA
Base Current	Ів	Vce = 30V, VBE = 0.5V	-	50	nA
DC Current Gain	hfe	Ic = 0.1mA, VcE = 10V Ic = 1mA, VcE = 10V Ic = 10mA, VcE = 10V *Ic = 150mA, VcE = 10V *Ic = 500mA, VcE = 10V	-	>35 >50 >75 100 - 300 >30	-

\*Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤2%



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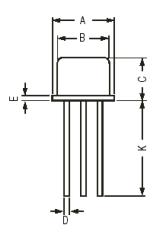


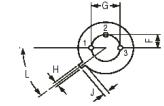
Description	Symbol Test Condition		Min.	Max.	Units
Small Signal Characteristics			<b>^</b>	n	
Collector Emitter Saturation Voltage	*Vce(sat)	Ic = 150mA, Iв = 15mA Ic = 500mA, Iв = 50mA	-	0.4 1.6	V
Base Emitter Saturation Voltage	*Vbe(sat)	Ic = 150mA, Iв = 15mA Ic = 500mA, Iв = 50mA	-	1.3 2.6	
Transition Frequency	**f⊤	Ic = 50mA, Vce = 20V f = 100MHz	200	-	MHz
Output Capacitance	Сово	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0 f = 100KHz	-	8	-5
Input Capacitance	Сіво	V <sub>BE</sub> = 2V, Ic = 0 f = 100KHz	-	30	pF

\*Pulse Test: Pulse Width ≤300µs, Duty Cycle ≤2%

\*\*fT is defined as the frequency at which /hFE/ extrapolates to unity

Description	Symbol	Test Condition	Min.	Max.	Units
Switching Time					
Delay Time	td		-	10	
Rise Time	tr	Ic = 150mA, IB1 = 15mA, Vcc = 30V	-	40	]
Turn on Time	ton	VCC - 30V	-	45	
Storage Time	ts		-	80	nS
Fall Time	tr	Ic = 150mA, IB1 = IB2 = 15mA, Vcc = 6V	-	30	]
Turn off Time	toff	VCC - 0V	-	100	]





Dim.	Α	В	С	D	Е	F	G	н	J	К	L
Min.	8.5	7.74	6.09	0.4	-	2.41	4.82	0.71	0.73	12.7	42°
Max.	9.39	8.5	6.6	0.53	0.88	2.66	5.33	0.86	1.02	-	48°

Dimensions : Millimetres

### Part Number Table

Description	Part Number		
Transistor, PNP, TO-39	2N2905		

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